

Supplementary Information for the manuscript

Influence of Alkali Metal Substitution on the Phase- Transition Behavior of CsGaQ₂ (Q = S, Se)

*Daniel Friedrich, Marc Schlosser, Martin Etter, and Arno Pfitzner**

*Prof. Dr. Arno Pfitzner

Institut für Anorganische Chemie, Universität Regensburg, Universitätsstraße 31, 93040

Regensburg, Germany

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The crystal structures of the high-temperature solid-solutions were refined by Rietveld refinement using X-ray diffraction data collected at a synchrotron. Details on these refinements can be found in the main paper.

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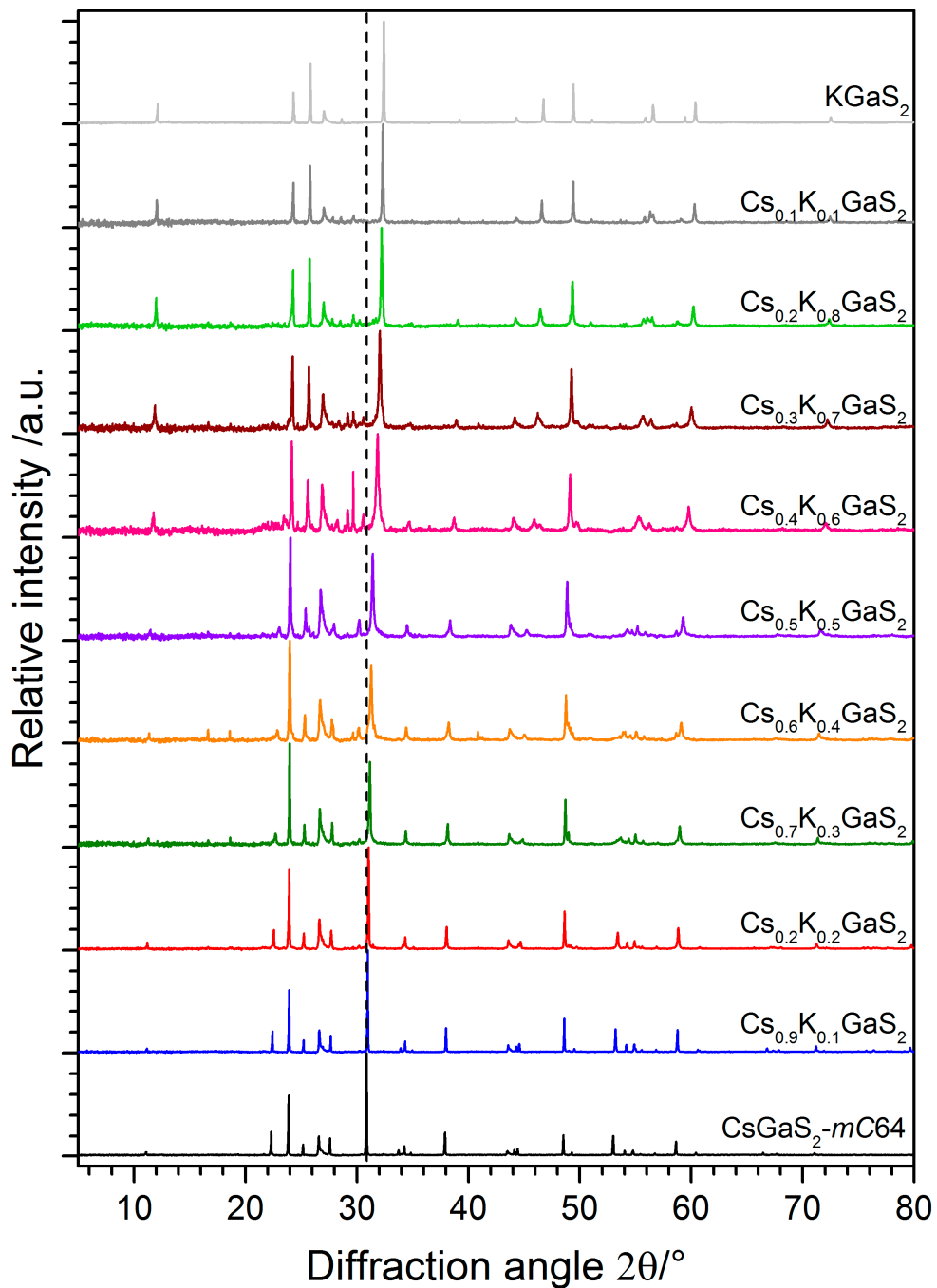


Figure S1 X-ray diffraction patterns (Cu- $K\alpha_1$ radiation, $\lambda = 1.540598 \text{ \AA}$) of each member of the solid solution series $\text{Cs}_{1-x}\text{K}_x\text{GaS}_2$ -mC64 ($x = 0 - 1$). The position of the strongest reflection of CsGaS_2 -mC64 is highlighted by a dashed line to visualize the 2θ shift.

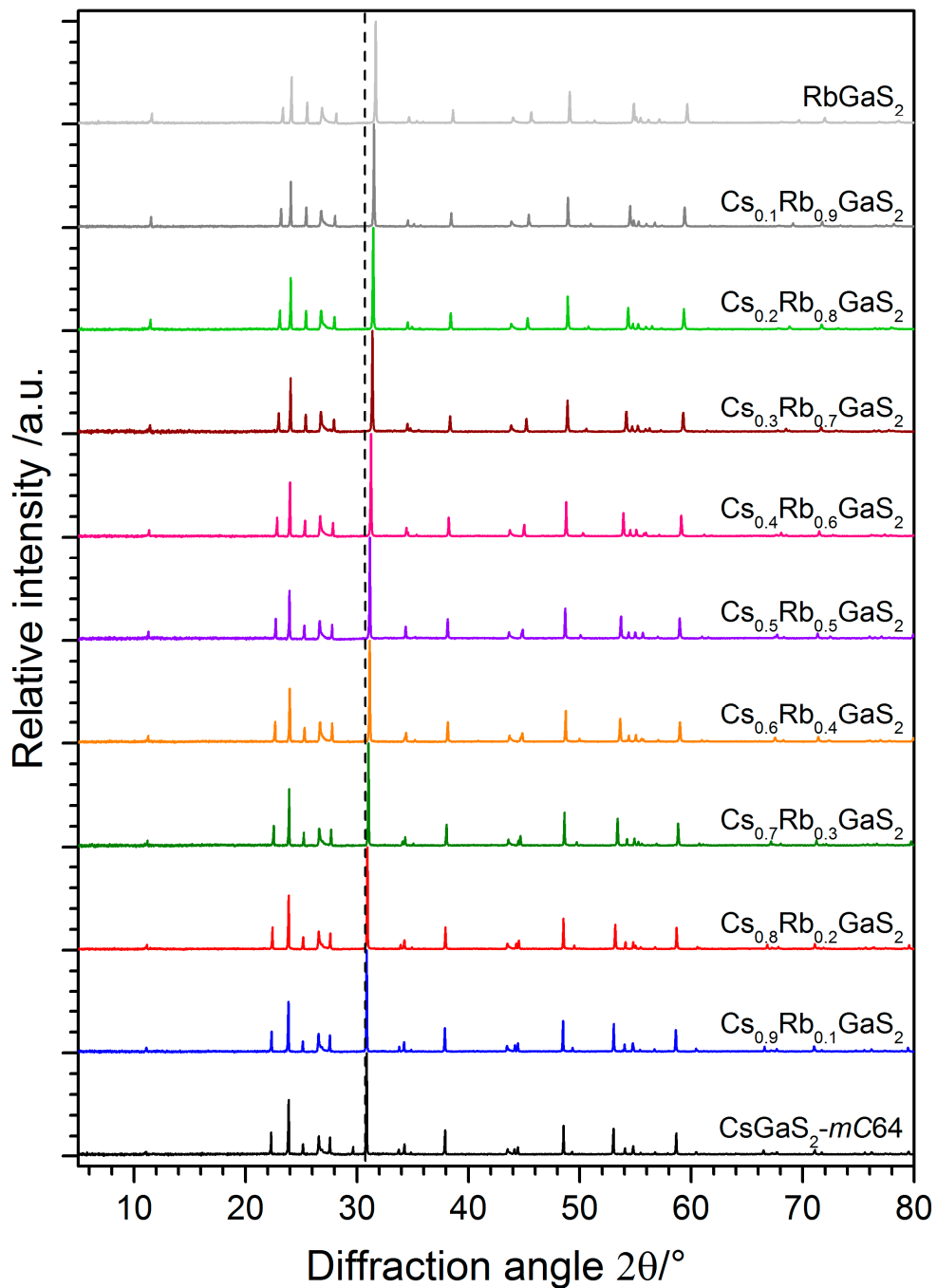


Figure S2 X-ray diffraction patterns (Cu- $K\alpha_1$ radiation, $\lambda = 1.540598 \text{ \AA}$) of each member of the solid solution series $\text{Cs}_{1-x}\text{Rb}_x\text{GaS}_2\text{-}m\text{C64}$ ($x = 0 - 1$). The position of the strongest reflection of $\text{CsGaS}_2\text{-}m\text{C64}$ is highlighted by a dashed line to visualize the 2θ shift.

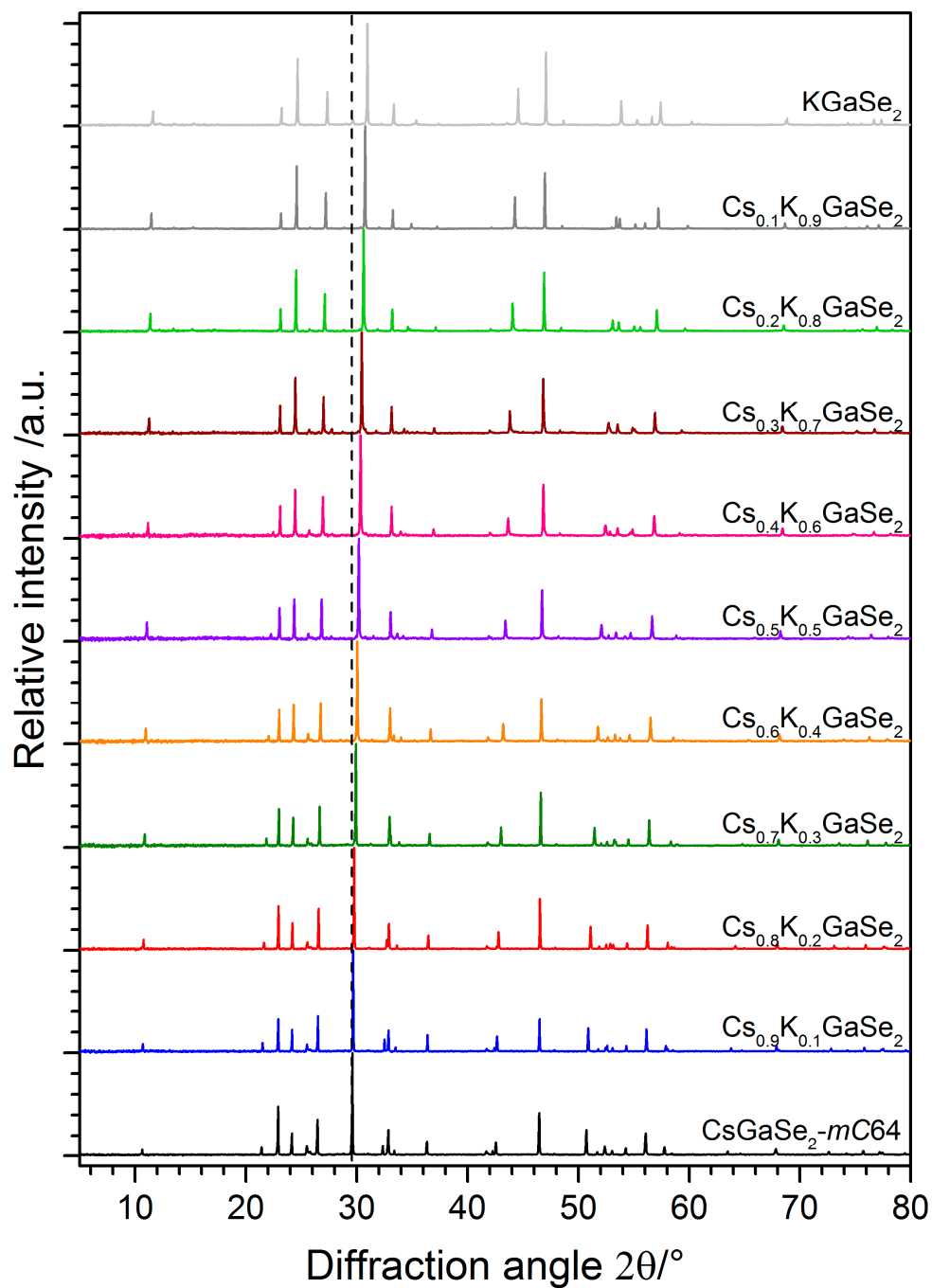


Figure S3 X-ray diffraction patterns (Cu- $K\alpha_1$ radiation, $\lambda = 1.540598 \text{ \AA}$) of each member of the solid solution series $\text{Cs}_{1-x}\text{K}_x\text{GaSe}_2$ -*m*C64 ($x = 0 - 1$). The position of the strongest reflection of CsGaSe_2 -*m*C64 is highlighted by a dashed line to visualize the 2θ shift.

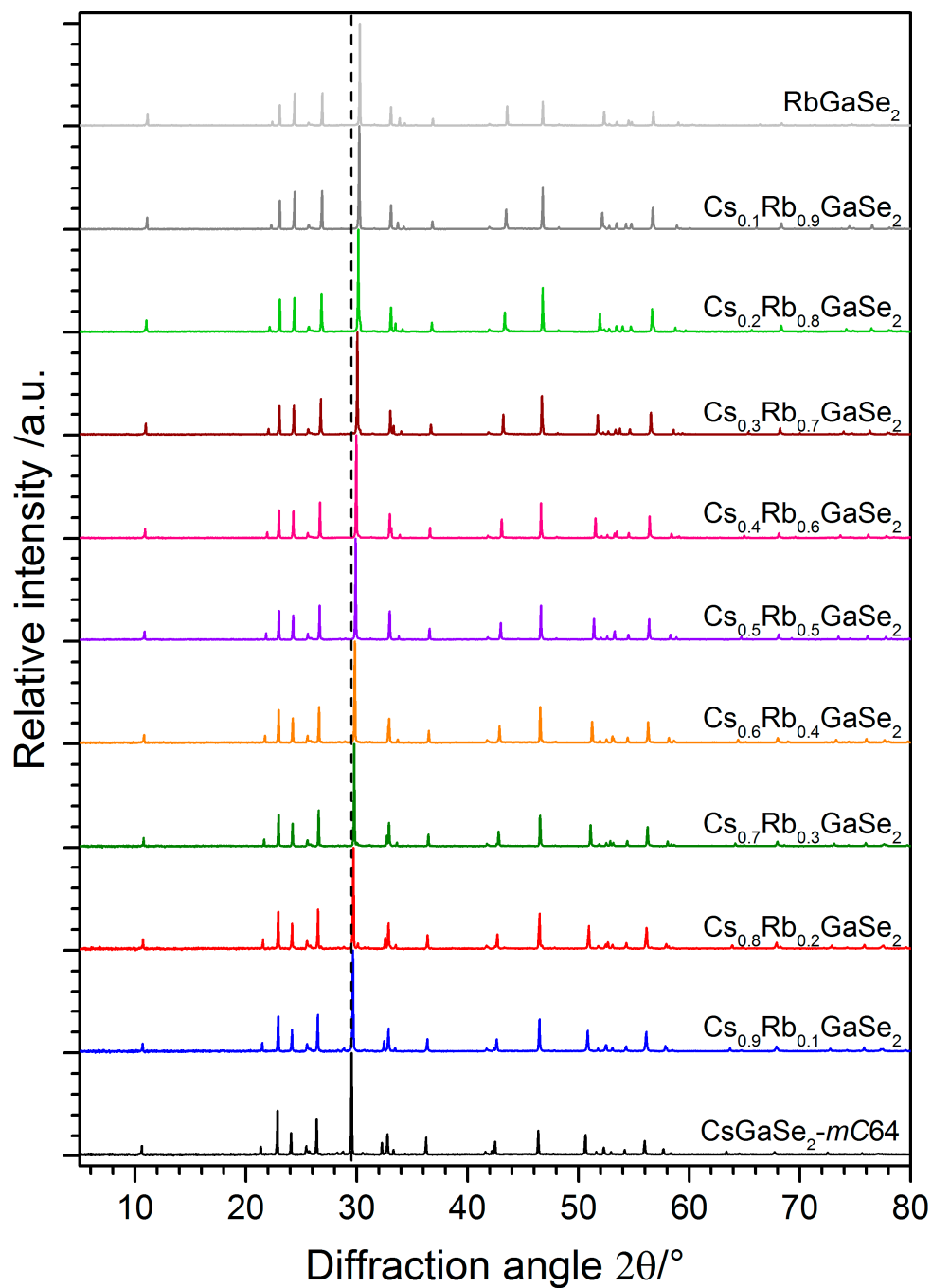


Figure S4 X-ray diffraction patterns (Cu- $K\alpha_1$ radiation, $\lambda = 1.540598 \text{ \AA}$) of each member of the solid solution series $\text{Cs}_{1-x}\text{Rb}_x\text{GaSe}_2$ -mC64 ($x = 0 - 1$). The position of the strongest reflection of CsGaSe_2 -mC64 is highlighted by a dashed line to visualize the 2θ shift.

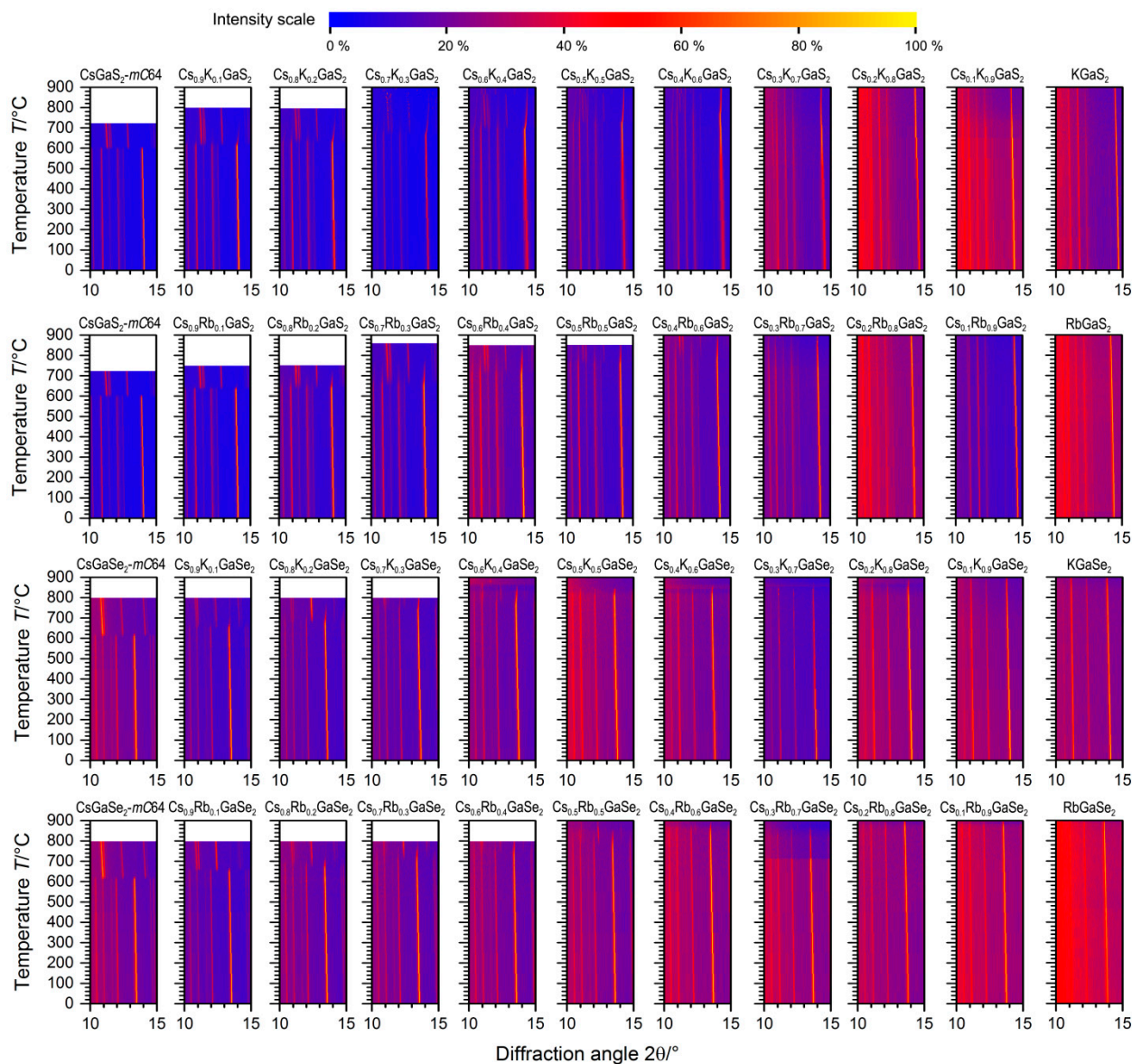


Figure S5 Evolution of the X-ray powder diffraction patterns of all solid solutions $\text{Cs}_{1-x}\text{M}_x\text{GaS}_2\text{-}m\text{C64}$ ($M = \text{K, Rb}$; $x = 0 - 1$) in the temperature range from 20 – 900 °C (Mo- $K\alpha_1$ radiation; $\lambda = 0.709300 \text{ \AA}$).

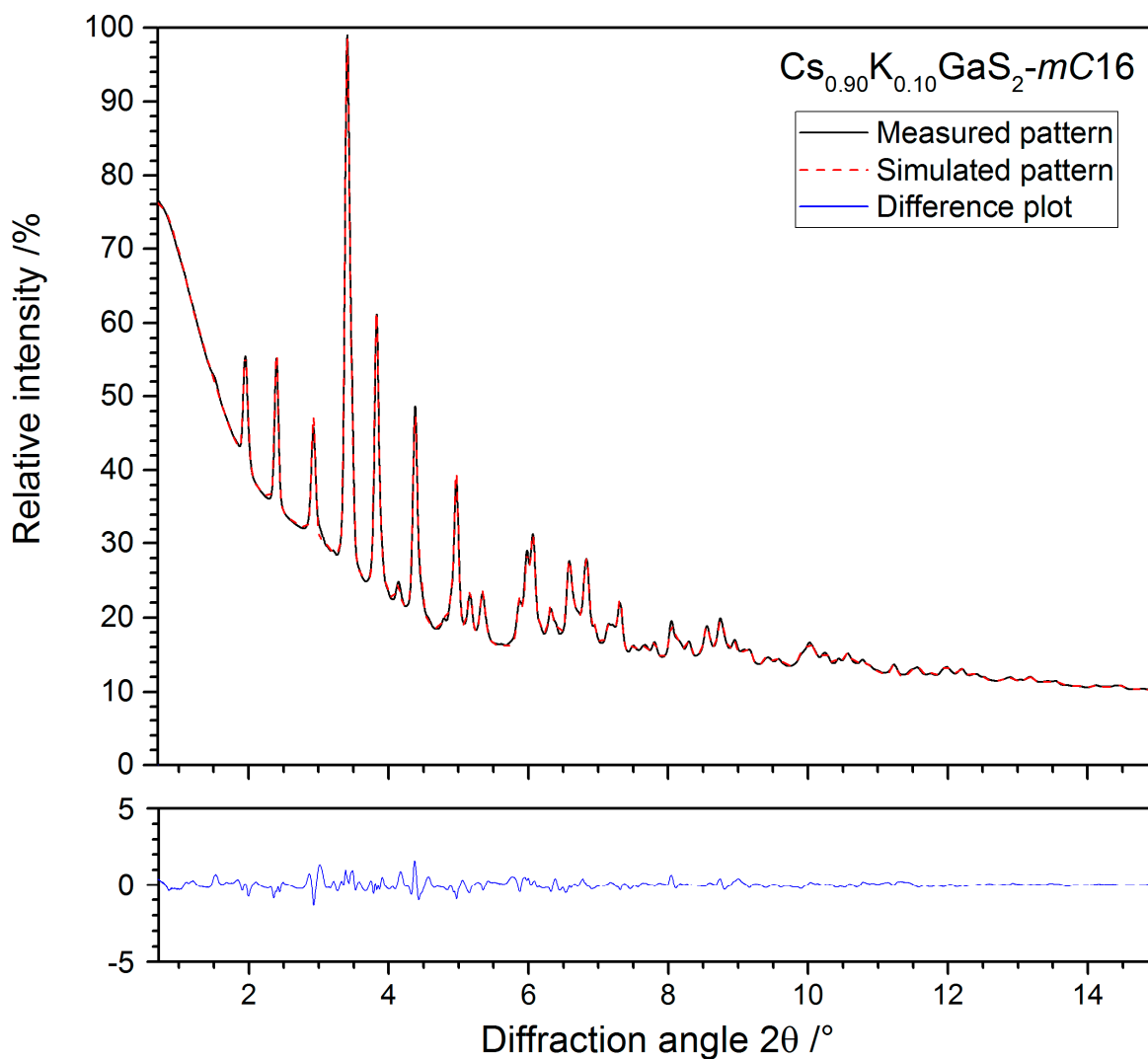


Figure S6 Rietveld refinement of the X-ray diffraction pattern of $\text{Cs}_{0.90}\text{K}_{0.10}\text{GaS}_2\text{-}m\text{C16}$ ($\lambda = 0.20717 \text{ \AA}$, $T = 20 \text{ }^\circ\text{C}$, 3201 data points) including the difference plot.

Table S1 Atomic coordinates and isotropic displacement parameters $U_{\text{iso}}/\text{\AA}^2$ for $\text{Cs}_{0.90}\text{K}_{0.10}\text{GaS}_2\text{-}m\text{C16}$ (20 °C).

Atom	<i>s.o.f.</i>	Wyck.	<i>x</i>	<i>y</i>	<i>z</i>	U_{iso}
Cs	0.90(1)*	4 <i>e</i>	0	0.145(1)*	¼	0.030(3)*
K	0.10*	4 <i>e</i>	0	0.145(1)*	¼	0.030(3)*
Ga	1	4 <i>e</i>	0	0.504(1)	¼	0.025(6)
S	1	8 <i>f</i>	0.179(2)	0.398(1)	0.093(2)	0.030(7)

* The coordinates, occupation factors, and displacement parameters of the Cs and K sites were refined using restraints to give a fully occupied alkali metal position in total. A *s.o.f.* of 1 means a fully occupied site, regardless its multiplicity.

Table S2 Anisotropic displacement parameters $U_{ij}/\text{\AA}^2$ for $\text{Cs}_{0.90}\text{K}_{0.10}\text{GaS}_2\text{-}m\text{C16}$ (20 °C).

Atom	U_{11}	U_{22}	U_{33}	U_{12}	U_{13}	U_{23}
Cs/K	0.03(1)	0.03(1)	0.03(1)	0	0.01(1)	0
Ga	0.02(1)	0.04(1)	0.03(1)	0	0.02(1)	0
S	0.04(1)	0.04(1)	0.01(1)	0.02(1)	0.01(1)	0.00(1)

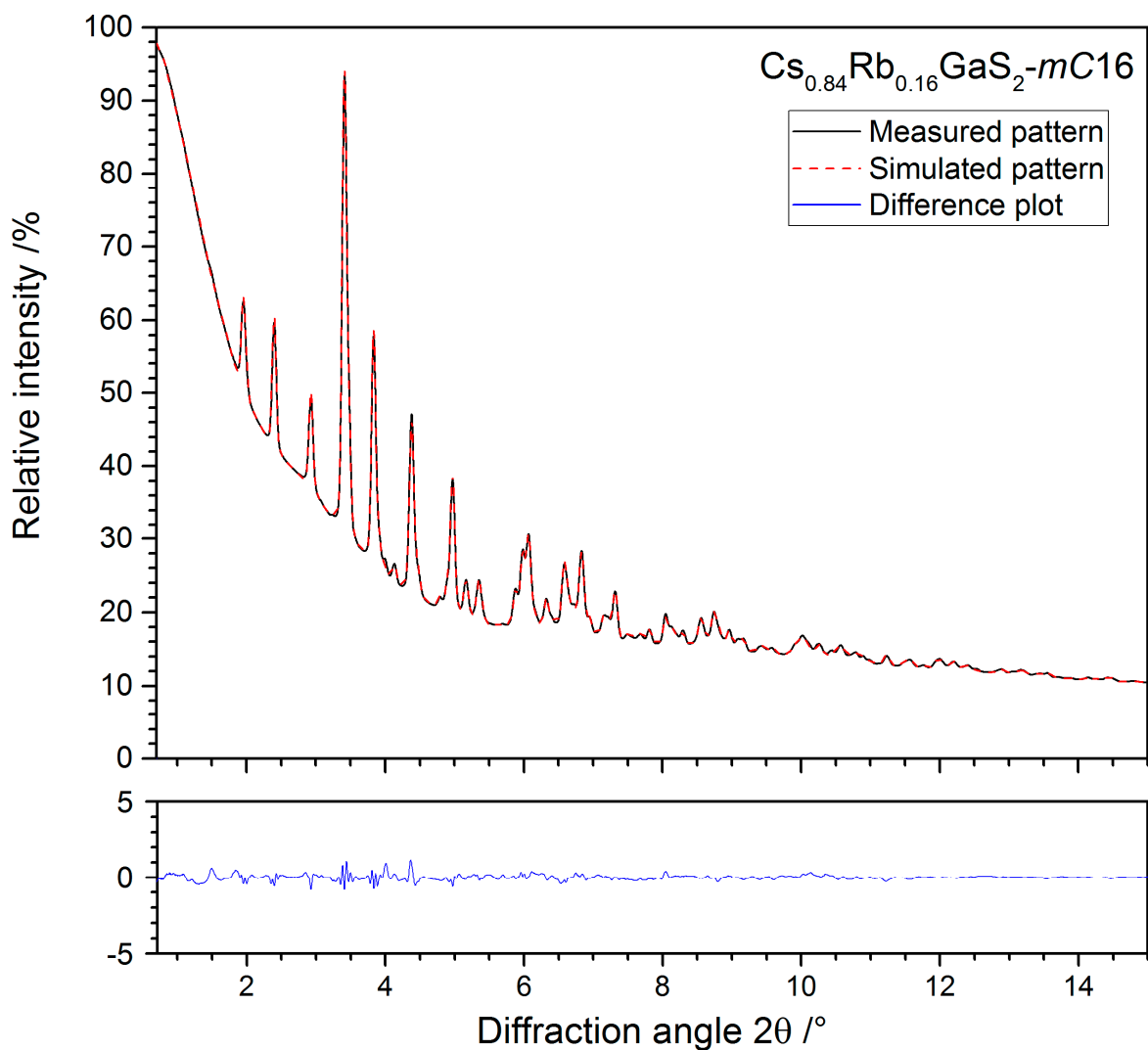


Figure S7 Rietveld refinement of the X-ray diffraction pattern of $\text{Cs}_{0.84}\text{Rb}_{0.16}\text{GaS}_2\text{-}m\text{C16}$ ($\lambda = 0.20717 \text{ \AA}$, $T = 20 \text{ }^\circ\text{C}$, 3201 data points) including the difference plot.

Table S3 Atomic coordinates and isotropic displacement parameters $U_{\text{iso}}/\text{\AA}^2$ for $\text{Cs}_{0.84}\text{Rb}_{0.16}\text{GaS}_2\text{-}m\text{C16}$ (20 °C).

Atom	<i>s.o.f.</i>	Wyck.	<i>x</i>	<i>y</i>	<i>z</i>	U_{iso}
Cs	0.84(1)*	4 <i>e</i>	0	0.145(1)*	¼	0.032(2)*
Rb	0.16*	4 <i>e</i>	0	0.145(1)*	¼	0.032(2)*
Ga	1	4 <i>e</i>	0	0.503(1)	¼	0.016(4)
S	1	8 <i>f</i>	0.182(1)	0.399(1)	0.094(1)	0.027(5)

* The coordinates, occupation factors, and displacement parameters of the Cs and K sites were refined using restraints to give a fully occupied alkali metal position in total. A *s.o.f.* of 1 means a fully occupied site, regardless its multiplicity.

Table S4 Anisotropic displacement parameters $U_{ij}/\text{\AA}^2$ for $\text{Cs}_{0.84}\text{Rb}_{0.16}\text{GaS}_2\text{-}m\text{C16}$ (20 °C).

Atom	U_{11}	U_{22}	U_{33}	U_{12}	U_{13}	U_{23}
Cs/Rb	0.04(1)	0.03(1)	0.03(1)	0	0.02(1)	0
Ga	0.02(1)	0.02(1)	0.01(1)	0	0.02(1)	0
S	0.04(1)	0.02(1)	0.01(1)	0.01(1)	0.00(1)	0.01(1)

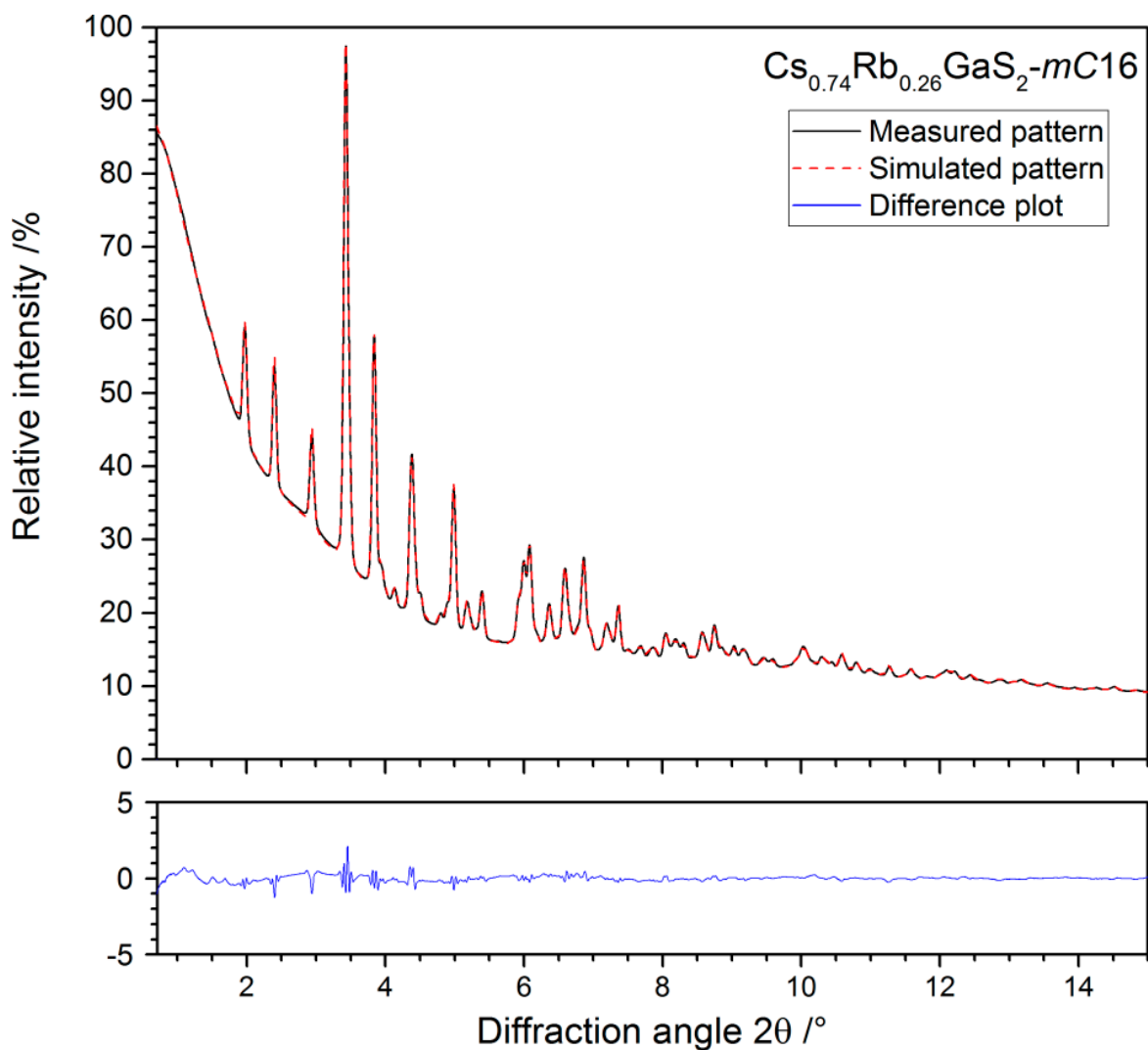


Figure S8 Rietveld refinement of the X-ray diffraction pattern of $\text{Cs}_{0.74}\text{Rb}_{0.26}\text{GaS}_2\text{-}m\text{C16}$ ($\lambda = 0.20717 \text{ \AA}$, $T = 20 \text{ }^\circ\text{C}$, 3201 data points) including the difference plot.

Table S5 Atomic coordinates and isotropic displacement parameters $U_{\text{iso}}/\text{\AA}^2$ for $\text{Cs}_{0.74}\text{Rb}_{0.26}\text{GaS}_2\text{-}m\text{C16}$ (20 °C).

Atom	<i>s.o.f.</i>	Wyck.	<i>x</i>	<i>y</i>	<i>z</i>	U_{iso}
Cs	0.76(1)*	4 <i>e</i>	0	0.145(1)*	¼	0.035(3)*
Rb	0.24*	4 <i>e</i>	0	0.145(1)*	¼	0.035(3)*
Ga	1	4 <i>e</i>	0	0.504(1)	¼	0.017(6)
S	1	8 <i>f</i>	0.181(1)	0.398(1)	0.095(2)	0.024(7)

* The coordinates, occupation factors, and displacement parameters of the Cs and K sites were refined using restraints to give a fully occupied alkali metal position in total. A *s.o.f.* of 1 means a fully occupied site, regardless its multiplicity.

Table S6 Anisotropic displacement parameters $U_{ij}/\text{\AA}^2$ for $\text{Cs}_{0.74}\text{Rb}_{0.26}\text{GaS}_2\text{-}m\text{C16}$ (20 °C).

Atom	U_{11}	U_{22}	U_{33}	U_{12}	U_{13}	U_{23}
Cs/Rb	0.03(1)	0.04(1)	0.04(1)	0	0.02(1)	0
Ga	0.02(1)	0.02(1)	0.03(1)	0	0.02(1)	0
S	0.03(1)	0.02(1)	0.01(1)	0.01(1)	0.02(1)	0.00(1)

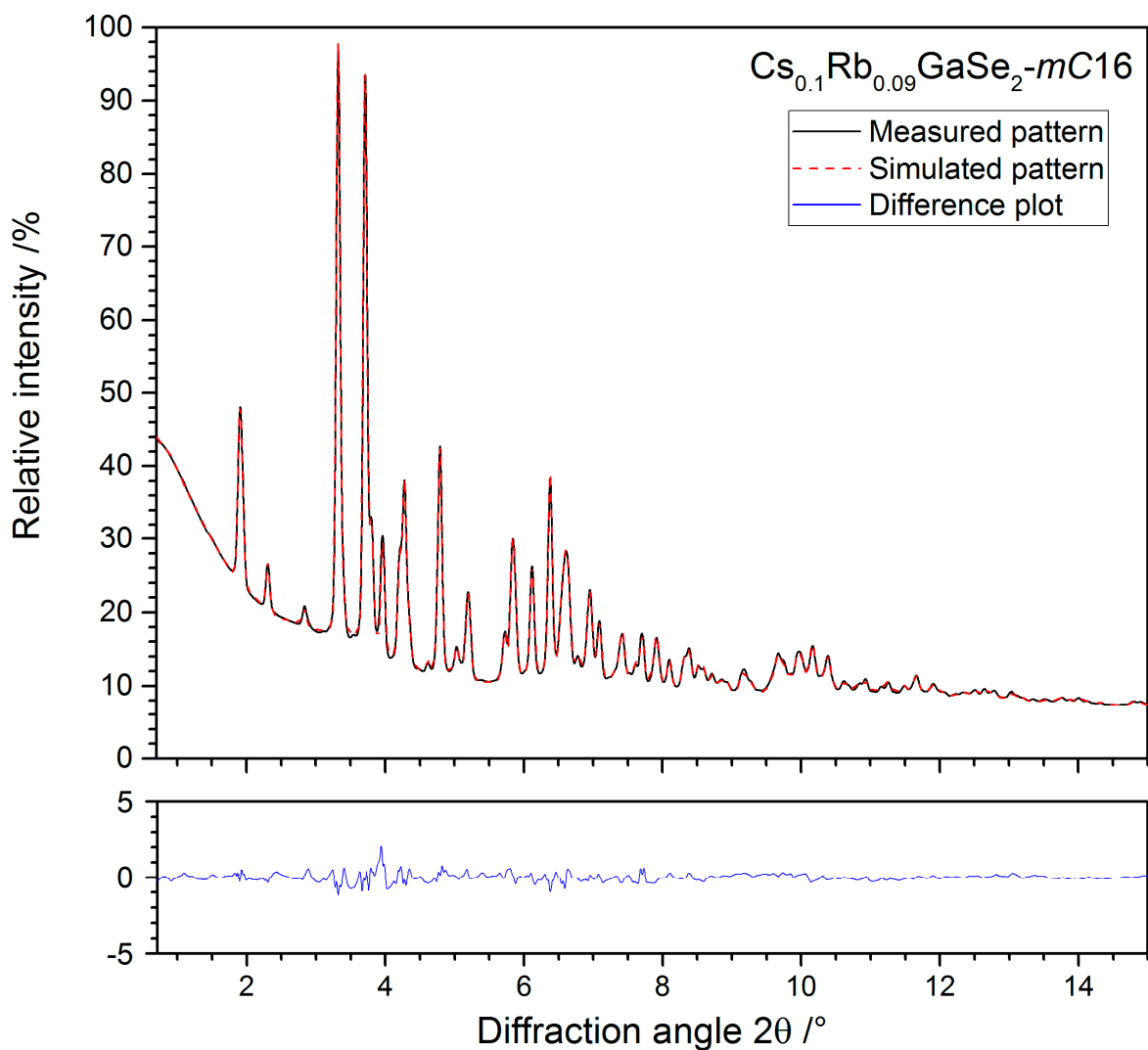


Figure S8 Rietveld refinement of the X-ray diffraction pattern of $\text{Cs}_{0.1}\text{Rb}_{0.09}\text{GaSe}_2\text{-}m\text{C16}$ ($\lambda = 0.20717 \text{ \AA}$, $T = 20 \text{ }^\circ\text{C}$, 3201 data points) including the difference plot.

Table S7 Atomic coordinates and isotropic displacement parameters $U_{\text{iso}}/\text{\AA}^2$ for $\text{Cs}_{0.91}\text{Rb}_{0.09}\text{GaS}_2\text{-}m\text{C16}$ (20 °C).

Atom	<i>s.o.f.</i>	Wyck.	<i>x</i>	<i>y</i>	<i>z</i>	U_{iso}
Cs	0.91(1)*	4 <i>e</i>	0	0.141(1)*	¼	0.036(5)*
Rb	0.09*	4 <i>e</i>	0	0.141(1)*	¼	0.036(5)*
Ga	1	4 <i>e</i>	0	0.503(1)	¼	0.025(14)
Se	1	8 <i>f</i>	0.186(1)	0.394(1)	0.097(1)	0.032(4)

* The coordinates, occupation factors, and displacement parameters of the Cs and K sites were refined using restraints to give a fully occupied alkali metal position in total. A *s.o.f.* of 1 means a fully occupied site, regardless its multiplicity.

Table S8 Anisotropic displacement parameters $U_{ij}/\text{\AA}^2$ for $\text{Cs}_{0.91}\text{Rb}_{0.09}\text{GaS}_2\text{-}m\text{C16}$ (20 °C).

Atom	U_{11}	U_{22}	U_{33}	U_{12}	U_{13}	U_{23}
Cs/Rb	0.04(1)	0.04(1)	0.04(1)	0	0.04(1)	0
Ga	0.03(1)	0.03(1)	0.03(2)	0	0.02(3)	0
Se	0.05(1)	0.03(1)	0.02(1)	0.02(1)	0.02(1)	0.01(1)

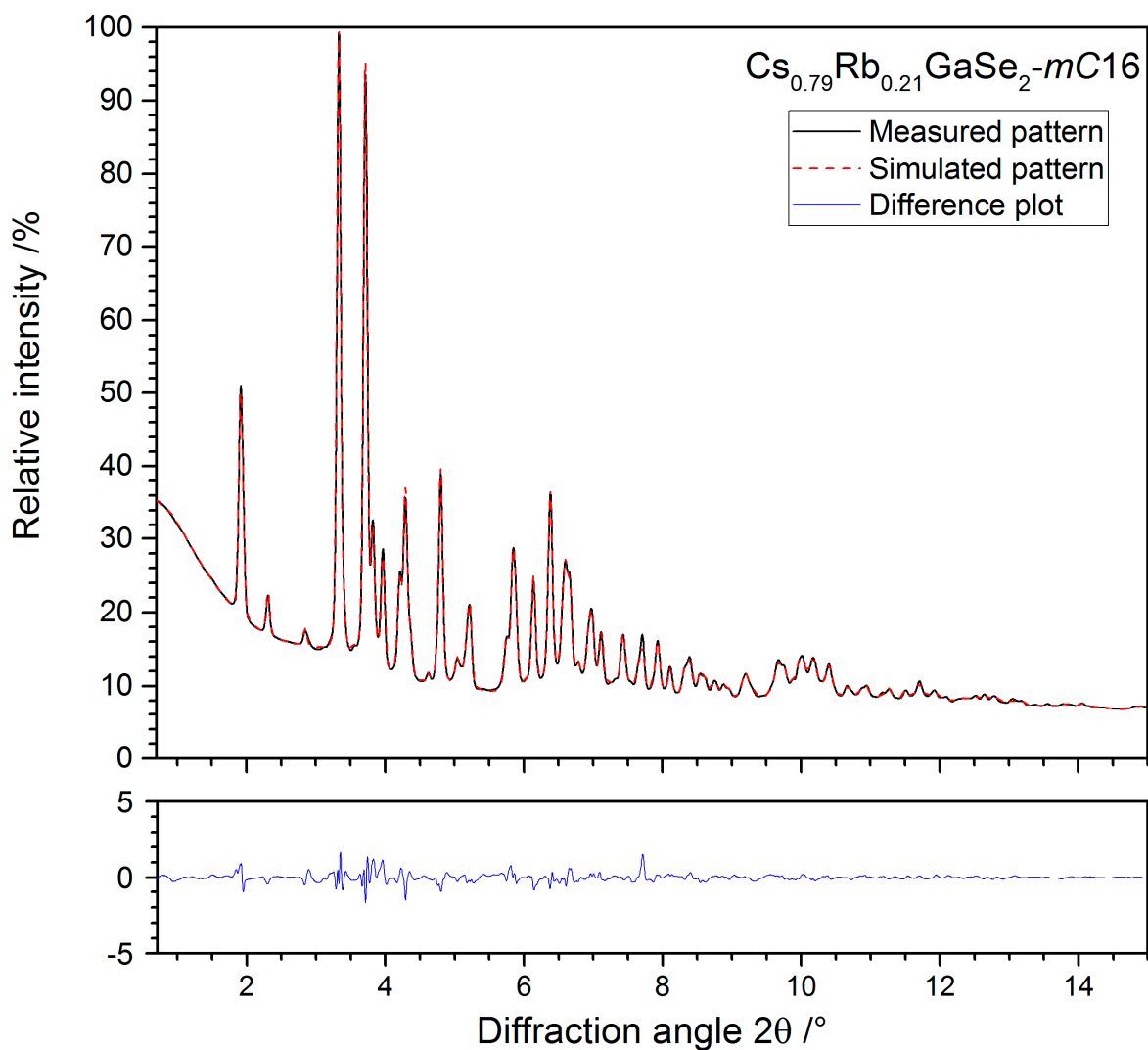


Figure S10 Rietveld refinement of the X-ray diffraction pattern of $\text{Cs}_{0.79}\text{Rb}_{0.21}\text{GaSe}_2\text{-}m\text{C16}$ ($\lambda = 0.20717 \text{ \AA}$, $T = 20 \text{ }^\circ\text{C}$, 3201 data points) including the difference plot.

Table S9 Atomic coordinates and isotropic displacement parameters $U_{\text{iso}}/\text{\AA}^2$ for $\text{Cs}_{0.79}\text{Rb}_{0.21}\text{GaSe}_2\text{-}m\text{C16}$ (20 °C).

Atom	<i>s.o.f.</i>	Wyck.	<i>x</i>	<i>y</i>	<i>z</i>	U_{iso}
Cs	0.79(1)*	4 <i>e</i>	0	0.141(1)*	¼	0.034(3)*
Rb	0.21*	4 <i>e</i>	0	0.141(1)*	¼	0.034(3)*
Ga	1	4 <i>e</i>	0	0.504(1)	¼	0.023(6)
Se	1	8 <i>f</i>	0.185(1)	0.394(1)	0.098(1)	0.030(3)

* The coordinates, occupation factors, and displacement parameters of the Cs and K sites were refined using restraints to give a fully occupied alkali metal position in total. A *s.o.f.* of 1 means a fully occupied site, regardless its multiplicity.

Table S10 Anisotropic displacement parameters $U_{ij}/\text{\AA}^2$ for $\text{Cs}_{0.79}\text{Rb}_{0.21}\text{GaSe}_2\text{-}m\text{C16}$ (20 °C).

Atom	U_{11}	U_{22}	U_{33}	U_{12}	U_{13}	U_{23}
Cs/Rb	0.04(1)	0.03(1)	0.03(1)	0	0.01(1)	0
Ga	0.02(1)	0.03(1)	0.03(1)	0	0.01(1)	0
Se	0.04(1)	0.03(1)	0.03(1)	0.01(1)	0.03(1)	0.01(1)